

Case No. **62601-CON2**

**DIRECTOR, U.S. PATENT AND TRADEMARK OFFICE
WASHINGTON, DC 20231**

In re Application of: **MEARS**
Serial No.: **NOT YET ASSIGNED**
Filed: **HEREWITH**
For: **SEMICONDUCTOR DEVICE INCLUDING
BAND-ENGINEERED SUPERLATTICE**

Sir:

Transmitted herewith is an INFORMATION DISCLOSURE STATEMENT in the above-identified application.

1. ☒ This IDS is submitted under 37 C.F.R. § 1.97. No fee is required.
2. ☐ This IDS is submitted under 37 C.F.R. § 1.97(c). Enclosed is a check in the amount of \$ 180.00.
3. ☐ This IDS is submitted under 37 C.F.R. § 1.97(c) and (e). No fee is required.
4. ☐ This IDS is submitted under 37 C.F.R. § 1.97(d) and (e). Enclosed is a check in the amount of \$130.00 to cover the petition fee.
5. ☒ The Commissioner is hereby authorized to charge or credit any discrepancies in fee amounts to Deposit Account No. 01-0484.
6. ☒ Please associate this application with Customer No. 27975.



27975

PATENT TRADEMARK OFFICE

Date: November 19, 2003

CHRISTOPHER F. REGAN
Reg. No. 34,906

In re Patent Application of:)
MEARS)
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INFORMATION DISCLOSURE STATEMENT	Atty Docket: Serial No.: Applicant: Filing Date: Group:	62601_CON2 Not Yet Assigned MEARS Herewith

U.S. PATENT DOCUMENTS							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90
	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannopoulos et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smimov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
	AQ	2003/ 0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
	AR	2003/ 0057416	03/27/03	Currie et al.	257	19	09/20/02
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
	AS	02/103767	12/27/02	WO	H01L	21/20	
	AT	2,347,520	09/06/00	GB	G02B	5/18	
	AU						

EXAMINER:	DATE CONSIDERED:
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>	

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OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society; Vol. 89, Number 7
	AW	R. Tsu; University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/06/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	

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